

## EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L13	0	"PG-PUBS INTERFERENCE SEARCH"	US-PGPU B; USPAT	OR	ON	2007/02/14 14:47
L2	0	("2005/0161430").URPN.	USPAT	OR	ON	2007/02/14 14:29
L7	1	((method process) and (Si silicon) and (atomic adj force adj microscope AFM) and (probe tip) and (mask\$4 resist photoresist) and dop\$4 and etch\$4 and anisotropic and fusion adj bond\$4 and cavity).clm.	US-PGPU B; USPAT	OR	ON	2007/02/14 14:32
L5	1	((method process) and (Si silicon) and (atomic adj force adj microscope AFM) and tip and (mask\$4 resist photoresist) and dop\$4 and etch\$4 and anisotropic and fusion adj bond\$4 and cavity and release and etch\$4).clm.	US-PGPU B; USPAT	OR	ON	2007/02/14 14:31
L4	1	((method process) and (Si silicon) and (atomic adj force adj microscope AFM) and tip and (mask\$4 resist photoresist) and dop\$4 and etch\$4 and anisotropic and fusion adj bond\$4 and cavity and release with etch\$4).clm.	US-PGPU B; USPAT	OR	ON	2007/02/14 14:30

## EAST Search History

L6	1	((method process) and (Si silicon) and (atomic adj force adj microscope AFM) and tip and (mask\$4 resist photoresist) and dop\$4 and etch\$4 and anisotropic and fusion adj bond\$4 and cavity).clm.	US-PGPU B; USPAT	OR	ON	2007/02/14 14:31
L3	1	((method process) and (Si silicon) and (atomic adj force adj microscope AFM) and tip and (mask\$4 resist photoresist) and dop\$4 with (silicon Si) and etch\$4 and anisotropic and fusion adj bond\$4 and cavity and release with etch\$4).clm.	US-PGPU B; USPAT	OR	ON	2007/02/14 14:30
L1	1	((method process) and (Si silicon) and (atomic adj force adj microscope AFM) same tip and (mask\$4 resist photoresist) and dop\$4 with (silicon Si) and etch\$4 and pyramidal and opposite\$4 with dop\$4 and anisotropic and fusion adj bond\$4 and cavity and release with etch\$4).clm.	US-PGPU B; USPAT	OR	ON	2007/02/14 14:29
L8	1	((Si silicon) and (atomic adj force adj microscope AFM) and (probe tip) and (mask\$4 resist photoresist) and dop\$4 and etch\$4 and anisotropic and fusion adj bond\$4 and cavity).clm.	US-PGPU B; USPAT	OR	ON	2007/02/14 14:33

## EAST Search History

L9	1	((Si silicon) and (atomic adj force adj microscope AFM) and (probe tip) and (mask\$4 resist photoresist) and dop\$4 and etch\$4 and anisotropic and fusion adj bond\$4).clm.	US-PGPU B; USPAT	OR	ON	2007/02/14 14:33
L10	3	((Si silicon) and (atomic adj force adj microscope AFM) and (probe tip) and (mask\$4 resist photoresist) and dop\$4 and etch\$4 and anisotropic).clm.	US-PGPU B; USPAT	OR	ON	2007/02/14 14:41
L11	8	((Si silicon) and (atomic adj force adj microscope AFM) and (probe tip) and (mask\$4 resist photoresist) and dop\$4 and etch\$4).clm.	US-PGPU B; USPAT	OR	ON	2007/02/14 14:47
L12	5	11 not 10	US-PGPU B; USPAT	OR	ON	2007/02/14 14:41

## EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S103	2	(( p+ "P.sup.+" ) and diode adj junction) with stop\$4	US-PGPU B; USPAT; EPO; JPO; DERWEN T; IBM_TDB	OR	OFF	2006/09/27 20:38
S104	2	(( "p+" "P.sup.+" ) and diode adj junction) with stop\$4	US-PGPU B; USPAT; EPO; JPO; DERWEN T; IBM_TDB	OR	OFF	2006/09/27 20:38
S105	10	(( "p+" "P.sup.+" ) and diode adj junction) same stop\$4	US-PGPU B; USPAT; EPO; JPO; DERWEN T; IBM_TDB	OR	OFF	2006/09/27 20:38
S86	332	( p+ "P.sup.+" )with (impurity diffusion adj layer) with stop\$4	US-PGPU B; USPAT; EPO; JPO; DERWEN T; IBM_TDB	OR	OFF	2006/09/27 20:36
S102	35	(cantilever probe adj tip) and diode adj junction and electrochemical\$4 adj etch\$4	US-PGPU B; USPAT	OR	ON	2006/09/27 19:29

## EAST Search History

S101	50	(cantilever probe adj tip) and diode adj junction and electrochemical	US-PGPU B; USPAT	OR	ON	2006/09/27 19:29
S100	108	(cantilever probe adj tip) and diode adj junction	US-PGPU B; USPAT	OR	ON	2006/09/27 19:29
S99	40	(cantilever probe adj tip) and oppositely adj doped	US-PGPU B; USPAT	OR	ON	2006/09/27 19:28
S98	8	S97 not S96	US-PGPU B; USPAT	OR	ON	2006/09/27 19:06
S97	24	(US-20060057757-\$ or US-20040139794-\$ or US-20030202456-\$).did. or (US-6886395-\$ or US-6694805-\$ or US-5994160-\$ or US-5717132-\$ or US-5367165-\$ or US-4943719-\$ or US-4668865-\$ or US-4685996-\$ or US-4307507-\$ or US-5021364-\$ or US-5066358-\$ or US-6156216-\$ or US-6794296-\$ or US-6680900-\$ or US-6281621-\$ or US-5962958-\$ or US-5883387-\$ or US-5116462-\$ or US-5087124-\$).did. or (JP-2002361595-\$).did. or (DE-19504552-\$).did.	US-PGPU B; USPAT; JPO; DERWENT	OR	ON	2006/09/27 19:01

## EAST Search History

S96	16	(US-20040139794-\$ or US-20030202456-\$).did. or (US-5994160-\$ or US-5367165-\$ or US-4943719-\$ or US-4668865-\$ or US-4307507-\$ or US-5066358-\$ or US-6156216-\$ or US-6794296-\$ or US-6680900-\$ or US-6281621-\$ or US-5883387-\$ or US-5116462-\$).did. or (JP-2002361595-\$).did. or (DE-19504552-\$).did.	US-PGPU B; USPAT; JPO; DERWEN T	OR	ON	2006/09/27 19:01
S94	0	(etch\$4 layer) with stop\$4 WITH diode adj junction not S93	US-PGPU B; USPAT; EPO; JPO; DERWEN T; IBM_TD B	OR	OFF	2006/09/27 18:31
S95	17	(etch\$4 layer) with stop\$4 same diode adj junction not S93	US-PGPU B; USPAT; EPO; JPO; DERWEN T; IBM_TD B	OR	OFF	2006/09/27 18:31
S93	3	(etch\$4 layer) NEAR3 stop\$4 WITH diode adj junction	US-PGPU B; USPAT; EPO; JPO; DERWEN T; IBM_TD B	OR	OFF	2006/09/27 18:30

## EAST Search History

S90	2	boron near2 stop\$4 same diode	US-PGPU B; USPAT; EPO; JPO; DERWEN T; IBM_TD B	OR	OFF	2006/09/27 18:27
S92	428	(etch\$4 layer) NEAR3 stop\$4 WITH diode	US-PGPU B; USPAT; EPO; JPO; DERWEN T; IBM_TD B	OR	OFF	2006/09/27 18:27
S91	928	(etch\$4 layer) NEAR3 stop\$4 same diode	US-PGPU B; USPAT; EPO; JPO; DERWEN T; IBM_TD B	OR	OFF	2006/09/27 18:27
S89	0	boron near2 stop\$4 same diode adj junction	US-PGPU B; USPAT; EPO; JPO; DERWEN T; IBM_TD B	OR	OFF	2006/09/27 18:26

## EAST Search History

S88	0	boron adj etch\$4 adj stop\$4 same diode adj junction	US-PGPU B; USPAT; EPO; JPO; DERWEN T; IBM_TD B	OR	OFF	2006/09/27 18:25
S87	2	( p+ "P.sup.+") with (impurity diffusion adj layer) with stop\$4 and diode adj junction	US-PGPU B; USPAT; EPO; JPO; DERWEN T; IBM_TD B	OR	OFF	2006/09/27 18:25
S85	6	S73 not S74	US-PGPU B; USPAT	OR	ON	2006/04/20 12:12
S83	22	S76 and S82	US-PGPU B; USPAT	OR	ON	2006/04/20 11:41
S84	2	S79 S80 S81	US-PGPU B; USPAT	OR	ON	2006/04/20 11:40
S79	2	S76 and S77	US-PGPU B; USPAT	OR	ON	2006/04/20 11:40
S80	1	S76 and S78	US-PGPU B; USPAT	OR	ON	2006/04/20 11:39
S81	2	S76 and S73	US-PGPU B; USPAT	OR	ON	2006/04/20 11:39



## EAST Search History

S82	8190	(AFM STEM SEM nanotip\$3 probe atomic adj force scanning near microscope) and ((si silicon) near (n p dop\$4) n-type p-type) and etch\$3	US-PGPU B; USPAT	OR	ON	2006/04/20 11:39
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## EAST Search History

S76	298	(US-5632382-\$ or US-5569626-\$ or US-4940505-\$ or US-5849627-\$ or US-4443930-\$ or US-5242505-\$ or US-5316615-\$ or US-5628834-\$ or US-6180869-\$ or US-4609968-\$ or US-4623912-\$ or US-5719410-\$ or US-5746826-\$ or US-5888906-\$ or US-6020247-\$ or US-6154475-\$ or US-6156216-\$ or US-6225154-\$ or US-4359367-\$ or US-4409424-\$ or US-4419604-\$ or US-4575462-\$ or US-4608271-\$ or US-4794064-\$ or US-4845049-\$ or US-4859554-\$).did. or (US-4894693-\$ or US-4905066-\$ or US-4912542-\$ or US-4977050-\$ or US-4999314-\$ or US-5198285-\$ or US-5200029-\$ or US-5231294-\$ or US-5286340-\$ or US-5308794-\$ or US-5376798-\$ or US-5396066-\$ or US-5431964-\$ or US-5434109-\$ or US-5580800-\$ or US-5723880-\$ or US-5808329-\$ or US-5888888-\$ or US-5899712-\$ or US-5917195-\$ or	USPAT	OR	ON	2006/04/20 11:38
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## EAST Search History

S78	16	(US-20030202456-\$ or US-20040139794-\$).did. or (US-6156216-\$ or US-4943719-\$ or US-6794296-\$ or US-5066358-\$ or US-5994160-\$ or US-5367165-\$ or US-4668865-\$ or US-4307507-\$ or US-6281621-\$ or US-5116462-\$ or US-5883387-\$ or US-6680900-\$).did. or (JP-2002361595-\$).did. or (DE-19504552-\$).did.	US-PGPU B; USPAT; JPO; DERWEN T	OR	ON	2006/04/20 11:38
S77	23	(US-20030202456-\$ or US-20040139794-\$ or US-20060057757-\$).did. or (US-6156216-\$ or US-5021364-\$ or US-6886395-\$ or US-4943719-\$ or US-6794296-\$ or US-6694805-\$ or US-5066358-\$ or US-5994160-\$ or US-5367165-\$ or US-5717132-\$ or US-4685996-\$ or US-4668865-\$ or US-4307507-\$ or US-6281621-\$ or US-5116462-\$ or US-5883387-\$ or US-5962958-\$ or US-6680900-\$).did. or (JP-2002361595-\$).did. or (DE-19504552-\$).did.	US-PGPU B; USPAT; JPO; DERWEN T	OR	ON	2006/04/20 11:38
S74	12	S66 S67	US-PGPU B; USPAT	OR	ON	2006/04/20 09:57

## EAST Search History

S75	3	"2002361595"	JPO; DERWEN T	OR	ON	2006/04/20 09:57
S65	70	("3977925"   "4307507"   "4312117"   "4668865"   "4685996"   "4806755"   "4912822"   "4916002"   "4943719"   "4968382"   "4968585").PN. OR ("2005/0161430"   "2006/0057757"   "5021364"   "5066358"). URPN.	US-PGPU B; USPAT; USOCR	OR	ON	2006/04/20 09:08
S73	18	S66 S67 S68 S69 S70 S71 S72	US-PGPU B; USPAT	OR	ON	2006/04/20 09:07
S56	48	S55 not S52	US-PGPU B; USPAT	OR	ON	2006/04/20 09:07
S72	2	(US-6794296-\$ or US-6281621-\$).did.	USPAT	OR	ON	2006/04/20 09:07
S71	4	(US-6680900-\$ or US-5994160-\$ or US-5066358-\$ or US-5021364-\$).did.	USPAT	OR	ON	2006/04/20 09:07
S50	42	deposit\$4 with (n-type p-type dop\$3) with (Si silicon) with (\$2AFM \$6probe \$6tip stylus)	US-PGPU B; USPAT	OR	ON	2006/04/20 09:06
S46	1	deposit\$4 near (n-type p-type dop\$3) near (Si silicon) near (\$2AFM \$6probe \$6tip stylus)	US-PGPU B; USPAT	OR	ON	2006/04/20 09:06
S70	1	(US-4943719-\$).did.	USPAT	OR	ON	2006/04/20 09:06
S69	6	(US-20040139794-\$ or US-20030202456-\$).did. or (US-6886395-\$ or US-6156216-\$ or US-5021364-\$ or US-4943719-\$).did.	US-PGPU B; USPAT	OR	ON	2006/04/20 09:06

## EAST Search History

S66	9	(US-6886395-\$ or US-6694805-\$ or US-5994160-\$ or US-5717132-\$ or US-5367165-\$ or US-4943719-\$ or US-4685996-\$ or US-4668865-\$ or US-4307507-\$).did.	USPAT	OR	ON	2006/04/20 09:03
S67	3	(US-20060057757-\$).did. or (US-5066358-\$ or US-5021364-\$).did.	US-PGPU B; USPAT	OR	ON	2006/04/20 09:03
S68	6	(US-20040139794-\$ or US-20030202456-\$).did. or (US-6886395-\$ or US-6156216-\$ or US-5021364-\$ or US-4943719-\$).did.	US-PGPU B; USPAT	OR	ON	2006/04/20 09:03
S64	4	(dop\$4 same (silicon si) same (microscope SEM AFM STEM cant?lever probe) same tip same etch\$4).clm.	US-PGPU B; USPAT	OR	ON	2006/04/19 18:05
S63	1	S61 not S62	US-PGPU B; USPAT	OR	ON	2006/04/19 18:03
S62	17	(US-20050208304-\$ or US-20030202456-\$ or US-20030098347-\$ or US-20040139794-\$ or US-20050142891-\$).did. or (US-5021364-\$ or US-4943719-\$ or US-5516404-\$ or US-6861791-\$ or US-6854648-\$ or US-6417673-\$ or US-6027951-\$ or US-5844251-\$ or US-6156216-\$ or US-6886395-\$ or US-5939833-\$ or US-6366266-\$).did.	US-PGPU B; USPAT	OR	ON	2006/04/19 18:00

## EAST Search History

S45	17	(n-type p-type dop\$3) near (Si silicon) near (\$2AFM \$6probe \$6tip stylus)	US-PGPU B; USPAT	OR	ON	2006/04/19 18:00
S44	218	(n-type p-type dop\$3) near (Si silicon) with (\$2AFM \$6probe \$6tip stylus)	US-PGPU B; USPAT	OR	ON	2006/04/19 17:59
S61	18	(n-type p-type dop\$3) near (Si silicon) near (\$2AFM \$6probe \$6tip stylus)	US-PGPU B; USPAT	OR	ON	2006/04/19 17:59
S13	5	(cant?lever AFM STEM SEM nanotip\$3 probe atomic scanning microscope) near2 tip with ((si silicon) near (n p dop\$4) n-type p-type) with etch\$3	US-PGPU B; USPAT	OR	ON	2006/04/19 17:58
S60	5	(cant?lever AFM STEM SEM nanotip\$3 probe atomic scanning microscope) near2 tip with ((si silicon) near (n p dop\$4) n-type p-type) with etch\$3	US-PGPU B; USPAT	OR	ON	2006/04/19 17:58